BAS21AHT1G

Low Leakage Switching Diode

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _R	Continuous Reverse Voltage	250	Vdc
V_{RRM}	V _{RRM} Repetitive Peak Reverse Voltage		Vdc
I _F	Peak Forward Current	200	mAdc
I _{FM(surge)}	Peak Forward Surge Current	625	mAdc

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
P _D	Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	200	mW
	Derate above 25°C	1.57	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	635	°C/W
T _J , T _{stg}	Junction and Storage Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 Minimum Pad

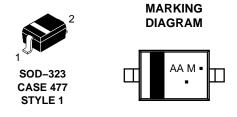


ON Semiconductor®

http://onsemi.com

LOW LEAKAGE SWITCHING DIODE





AA = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

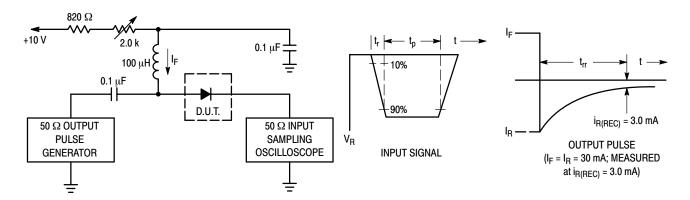
Device	Package	Shipping [†]
BAS21AHT1G	SOD-323 (Pb-Free)	3000/Tape & Reel
NSVBAS21AHT1G	SOD-323 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAS21AHT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Reverse Voltage Leakage Current $(V_R = 200 \text{ Vdc})$ $(V_R = 200 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I _R		- -	40 100	nAdc μAdc	
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	250	-	_	Vdc	
Forward Voltage (I _F = 100 mAdc) (I _F = 200 mAdc)	V _F	- -	- -	1000 1250	mV	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	_	5.0	pF	
Reverse Recovery Time $(I_F = I_R = 30 \text{ mAdc}, R_L = 100 \Omega)$	t _{rr}	-	50	_	ns	



Notes: 1. A 2.0 $k\Omega$ variable resistor adjusted for a Forward Current (I_F) of 30 mA.

- 2. Input pulse is adjusted so $I_{\mbox{\scriptsize R(peak)}}$ is equal to 30 mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

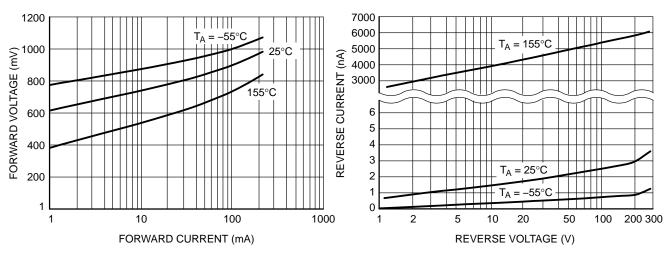
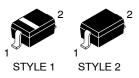


Figure 2. Forward Voltage

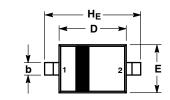
Figure 3. Reverse Leakage

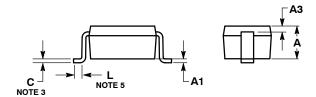


SOD-323 CASE 477-02 **ISSUE H**

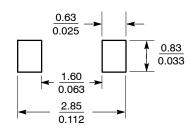
DATE 13 MAR 2007

SCALE 4:1





SOLDERING FOOTPRINT*

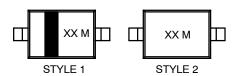


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS.
 5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES			
DIN	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.031	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A3	(0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016	
С	0.089	0.12	0.177	0.003	0.005	0.007	
D	1.60	1.70	1.80	0.062	0.066	0.070	
E	1.15	1.25	1.35	0.045	0.049	0.053	
L	0.08			0.003			
HE	2.30	2.50	2.70	0.090	0.098	0.105	

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

PIN 1. CATHODE (POLARITY BAND) 2. ANODE

NO POLARITY

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